



XTSD01G/XTSD02G/XTSD04G/XTSD08G

SD NAND

Datasheet

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CONTENTS

1. Introduction.....	3
2. Product List.....	3
3. Features.....	3
4. Physical Characteristic Temperature.....	3
5. Pin Assignments.....	4
6. Usage.....	5
6.1. Product Protocol.....	5
6.2. DC Characteristics.....	5
7. Package Dimensions.....	6
8. Ordering Information.....	7
9. Revision History.....	9

1. Introduction

XTX SD NAND is an embedded storage solution designed in a LGA8 package form. The operation of SD NAND is similar to an SD card which is an industry standard.

SD NAND consists of NAND flash and a high performance controller. 3.3V supply voltage is required for the NAND area (VCC). SD NAND is fully compliant with SD2.0 interface, which allows most of general CPU to utilize. SD NAND has high performance at a competitive cost, high quality and low power consumption.

2. Product List

Capacity	Part number	Package	Size
1Gb	XTSD01GLGEAG	LGA8 (Land Grid Array)	8x6mm
	XTSD01GDLGEGA	LGA8 (Land Grid Array)	8x6mm
	XTSD01GCLGEGA	LGA8 (Land Grid Array)	8x6mm
	XTSD01GBLGEGA	LGA8 (Land Grid Array)	8x6mm
2Gb	XTSD02GLGEAG	LGA8 (Land Grid Array)	8x6mm
4Gb	XTSD04GLGEAG	LGA8 (Land Grid Array)	8x6mm
	XTSD04GCLGEGA	LGA8 (Land Grid Array)	8x6mm
8Gb	XTSD08GLGEAG	LGA8 (Land Grid Array)	8x6mm
	XTSD08GCLGEGA	LGA8 (Land Grid Array)	8x6mm

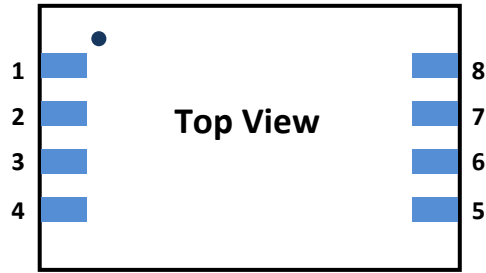
3. Features

- Support up to 50Mhz clock frequency
- Support 1/4 bit mode
- Built-in HW ECC Engine and highly reliable NAND management mechanism
- Write speed up to class 8
- Smaller package LGA8 (Land Grid Array)

4. Physical Characteristic Temperature

- Operation Conditions
Temperature Range: Ta = -30 to +85 degrees centigrade
- Storage Conditions
Temperature Range: Tstg = -40 to +85 degrees centigrade

5. Pin Assignments



Pin No.	Pin name (SD mode)	Pin name (SPI mode)
1	SD2, I/O pin	NC, no connection
2	SD3, I/O pin	/CS, chip select
3	CLK, clock signal	CLK, clock signal
4	Vss, ground	Vss, ground
5	CMD, command signal	DI, data in
6	SD0, I/O pin	DO, data out
7	SD1, I/O pin	NC, no connection
8	Vdd, power supply	Vdd, power supply

6. Usage

6.1. Product Protocol

As SD NAND is the realize SD2.0 standard product, thus please refer to the SD2.0 related protocol : SD Physical Layer Specification Version 2.00.

6.2. DC Characteristics

Item	Symbol	MIN	MAX	Unit	Note	
Supply voltage	VDD	2.7	3.6	V		
Input voltage	High Level	V _{IH}	VDD*0.625	VDD+0.3	V	
	Low Level	V _{IL}	VSS-0.3	VDD*0.25	V	
Output voltage	High Level	V _{OH}	VDD*0.75	--	V	I _{OH} =-2mA, VDD=VDDmin
	Low Level	V _{CL}	--	VDD*0.125	V	I _{OL} =2ma, VDD=VDDmin
Standby Current(*)	I _{cc1}	--	20*	mA	VDD=3.6V, clock 25MHz	
		--	0.2		VDD=3.0V, clock STOP, Ta=25° C	
Operation Current(*)	Write	I	--	30	mA	3.6V/25MHz,50MHz
	Read	I	--	30		
Input voltage setup Time	V _{rs}	--	250	ms		

Note: Standby current max 20mA with CLOCK 25Mhz only based on 100 pcs samples

Peak Voltage and Leak Current

Item	Symbol	MIN	MAX	Unit	Note
Peak voltage on all lines		-0.3	VDD+0.3	V	
Input Leakage Current for all pins		-10	10	uA	
Output Leakage Current for all outputs		-10	10	uA	

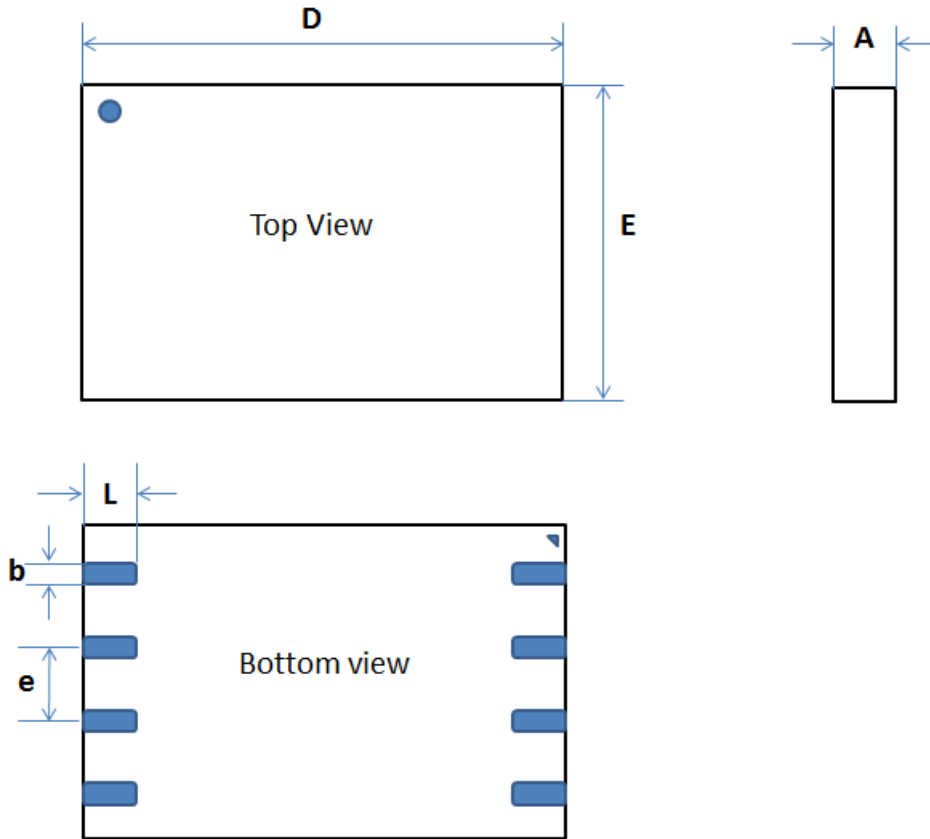
Signal Capacitance

Item	Symbol	MIN	MAX	Unit	Note
Pull up Resistance	R _{CMD} /R _{DAT}	10	100	k	
Total bus capacitance for each signal line	C _L	-	40	pF	1 card C _{HOST} +C _{BUS} ≤ 30pF
Card Capacitance for signal pin	C _{CARD}	-	10	pF	
Pull up Resistance inside card (pin1)	R _{DAT3}	10	90	k	
Capacity Connected to Power line	C _C	-	5	pF	

Note: WP pull-up (R_{wp}) Value is depend on the Host Interface drive circuit.

7. Package Dimensions

LGA8 (8*6mm) (Land Grid Array)

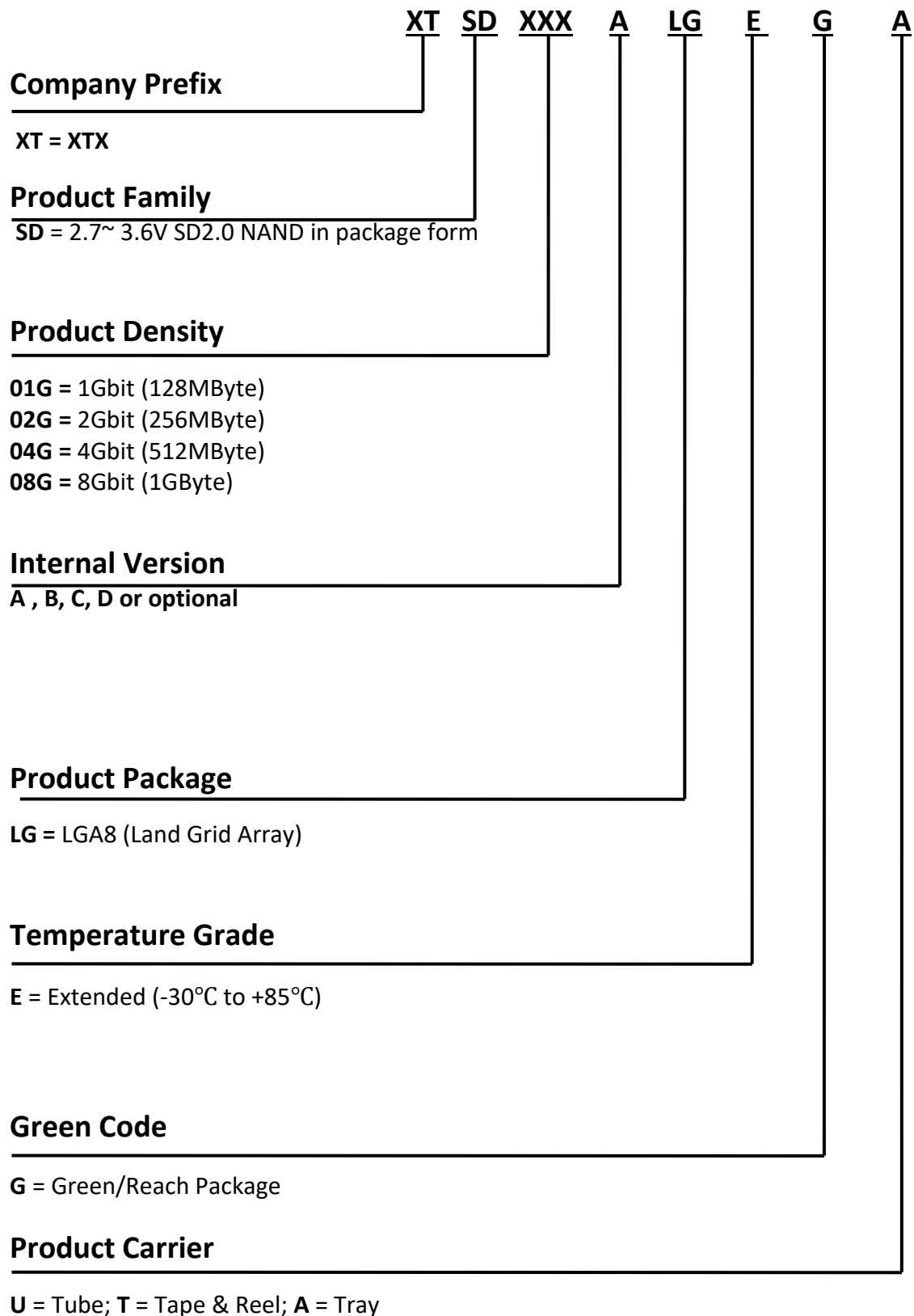


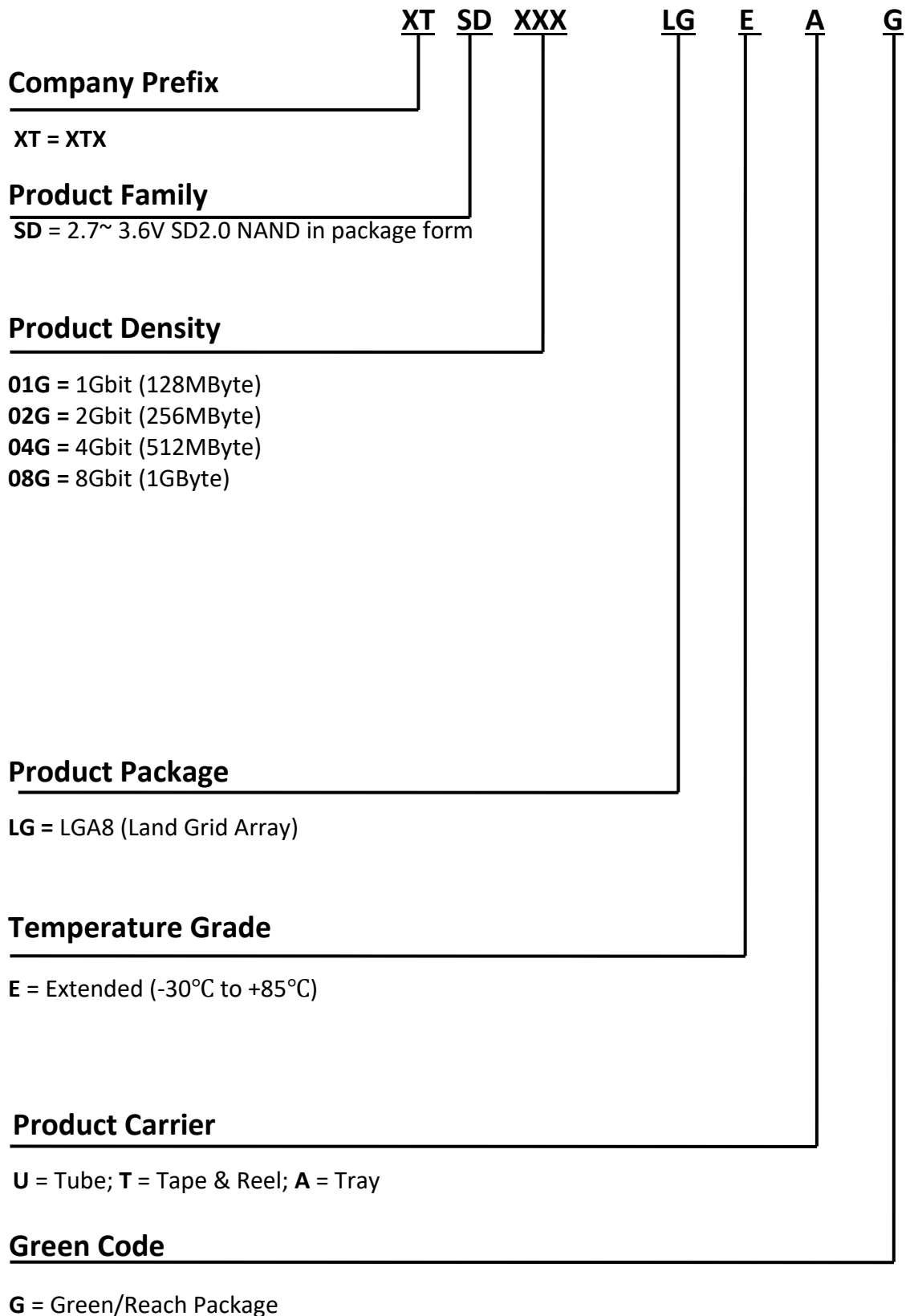
Dimensions

Symbol		A			b	D		E		e		L
Unit												
Mm	Min	0.85			0.55	7.95		5.95				0.75
	Norm	0.90			0.60	8.00		6.00		1.27		0.80
	Max	0.95			0.65	8.05		6.05				0.85

8. Ordering Information

The ordering part number is formed by a valid combination of the following





9. Revision History

Version No.	Change Description	Date
V1.0	Initial release, part number is based on extended temperature, WSON 8*6mm package, tape & reel packing, 1Gb/2Gb/4Gb density were included.	2017/1/10
V1.1	Add 8Gb density, and correct some typos;	2017/1/10
V2.1	Part number change from PNSDxxGWS to PNSDxxGLG; Package change from WSON8 to LGA8; Package dimension b change from 0.7mm to 0.6mm; Package dimension picture updated without the dissipating pad; Add a page for part number description;	2017/1/22
V2.2	Modify part number description; Page head re-layout;	2017/1/23
V2.3	Add SPI mode pin description	2017/2/1
V2.4	Set default Part number and PNSDxxGLGEAG (tray packing)	2017/2/14
V2.5	Part number update from PNSDxxxx to XTSDxxxx	2017/3/3
V2.6	Rename company name to XTX	2017/3/23
V2.7	Revise page #8,9 & 10 register table to include 8Gb, add cover page & page	2018/4/2
V2.8	Revise page #7 leakage unit error correction to uA.	2018/4/25
V2.9	Revise OPN to new ordering format & add new OPN, include manual content option	2018/10/23
V3.0	Remove the Incomplete SD protocol and correct the ordering information	2019/2/27
V3.1	Revise the ordering information	2019/5/15